

1 x 4 GaAs PIN Photodiode Array

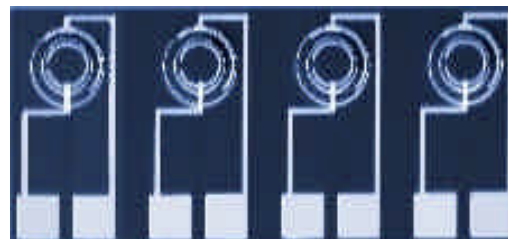
(preliminary information)

Product Description

EMCORE's 4 channel Gallium Arsenide (GaAs) PIN photodiode array is designed for multimode fiber applications. Utilizing EMCORE's own state-of-the-art MOCVD wafer foundry and device fabrication facility guarantees a reliable high volume fabrication source of package ready die to meet the growing needs of fiber optic component manufacturers. Excellent device performance and robust operation makes the 8485-1400 the superior device for multimode optical communication applications.

Features

- Data rates of 3.125 Gb/s per channel
- Excellent responsivity
- Uniform channel to channel characteristics
- Excellent crosstalk attenuation
- Low dark current



Product Specifications

Electro-Optical Characteristics (T = 30°C)

	Conditions	Min.	Typical	Max.	Unit
Speed		3.125			GHz
Responsivity	3 to -26 dBm, 850 nm Epoxy coated, n=1.6	.4	.5		A/W
Response Variation	3 to -26 dBm, 850 nm		2	3	%
Active Area (aperture)	-		70		μm
Crosstalk Attenuation	3 dBm, -1.6 V	30	40		dB
Rise/Fall Time	-1.6 V bias		32/75	50/100	ps
Dark Current	-1.6 V, -70 dBm		.5	3	nA
Capacitance	-1.6 V, 1 MHz	.35	.4	.5	pF
Reverse Breakdown	1 μA	20	50		V
Reflectivity	Epoxy coated, n=1.6			1	%

Physical Description

	Min.	Typical	Max.	Unit
Die Length	1035	1055	1075	μm
Die Width	430	450	470	μm
Die Height	600	625	650	μm
Diode Pitch		250		μm
Bond Pads		80x80		μm

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